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On 6/25/01 June 25, 2001

TOWNSEND and TOWNSEND and CREW LLP

By: Sara B. McPeak

Sara B. McPeak

PATENT
Attorney Docket No.: 00939-073600US

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Sang Young Kim et al.

Application No.: 09/434,736

Filed: November 2, 1999

For: METHOD FOR FILLING
CONTACT HOLES WITH METAL BY
TWO-STEP DEPOSITION

Examiner: E. T. Pert

Art Unit: 2813

AMENDMENT

Assistant Commissioner for Patents
U. S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

This is a response to the Office Action mailed March 23, 2001. Please amend the above-identified application as follows.

IN THE SPECIFICATION:

At column 3, after the paragraph ending on line 35 and before the paragraph beginning on line 36, please add the following paragraph:

Referring to Fig. 2A, in one embodiment of the present invention, a photoresist film is used to cover first insulating oxide layer 6. The photoresist film is then processed to create the contact pattern mask. Contact holes 30 are formed in first insulating oxide layer 6 as illustrated in Fig. 2A. The portion of contact holes 30 nearest gate electrode 5 or junction 2 are generally vertical. In some embodiments, such portions of the contact holes are at about a 90 degree angle to the top surface of silicon substrate 1. The upper

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